Abstracts

A New Large-Signal Model Based on Pulse Measurement Techniques for RF Power MOSFET

J.M. Collantes, J.J. Raoux, J.P. Villotte, R. Quere, G. Montoriol and F. Dupis. "A New Large-Signal Model Based on Pulse Measurement Techniques for RF Power MOSFET." 1995 MTT-S International Microwave Symposium Digest 95.3 (1995 Vol. III [MWSYM]): 1553-1556.

A large-signal model for RF power MOSFET has been obtained using a new characterization and extraction technique. This technique is based on pulsed I-V characteristics and pulsed S-parameters measurements, to take into account the thermal state of the device. A table-based model is used to represent the I-V drain current source. The complete large-signal model is implanted in an harmonic-balance commercial simulator and its accuracy is evidenced by a comparison with active load-pull measurements at L band.

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